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STPS10LCD100C

High voltage power Schottky rectifier

Features

- High junction temperature capability
- Good trade-off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified
- Insulated package TO-220FPAB
 - Insulated voltage: 2000 V_{RMS}
 - Typical package capacitance: 12 pF

Description

Dual center tap Schottky rectifier designed for high frequency switched mode power supplies.

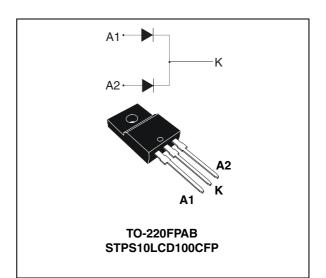


Table 1.Device summary

I _{F(AV)}	2 X 5 A
V _{RRM}	100 V
Тj	175 °C
V _F (typ)	0.64 V

Characteristics 1

Table 2. Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parameter			Value	Unit	
V _{RRM}	Repetitive peak reverse voltage			100	V	
I _{F(RMS)}	RMS forward current			30	А	
I	Average forward current, $\delta = 0.5$	per diode	T _c = 145 °C	5	A	
I _{F(AV)}		per device	T _c = 135 °C	10		
	Surge per repetitive forward surrent	t _p = 8.3 ms sinusoidal		155	А	
IFSM	Surge non repetitive forward current	t _p = 10 ms sinusoidal		150		
P _{ARM}	Repetitive peak avalanche power	t _p = 1 μs T _j =	25 °C	3360	W	
T _{stg}	Storage temperature range			-65 to + 175	°C	
Тj	Maximum operating junction temperature ⁽¹⁾			175	°C	
dV/dt	Critical rate of rise of reverse voltage			10000	V/µs	
. dD						

 $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid thermal runaway for a diode on its own heatsink 1.

Table 3. Thermal parameters

Symbol	Parameter		Value	Unit
Р	Junction to case	per diode	6.8	
R _{th(j-c)}	Junction to case	per device	4.9	°C/W
R _{th(c)}	Coupling		3.0	

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _B ⁽¹⁾	Reverse leakage current	$T_j = 25 \text{ °C}$			1.5	μA	
'R` ′	¹⁾ Reverse leakage current $T_j = 125 \text{ °C}$ $V_R = V_{RRM}$		0.4	1	mA		
		$\frac{T_j = 25 \text{ °C}}{T_j = 125 \text{ °C}} I_F = 5 \text{ A}$				0.84	v
V _F ⁽²⁾	Forward voltage drop		$I_F = 5 A$		0.64	0.70	v
VF.	Forward voltage drop	T _j = 25 °C	1 - 10 4			0.93	v
		T _i = 125 °C	I _F = 10 A		0.72	0.78	v

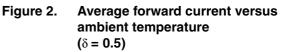
1. Pulse test: t_p = 5 ms, δ < 2 %

2. Pulse test: t_p = 380 µs, δ < 2 %

To evaluate the conduction losses use the following equation: P = 0.62 x $I_{F(AV)}$ + 0.016 x ${I_F}^2_{(RMS)}$



Figure 1. Average forward power dissipation versus average forward current



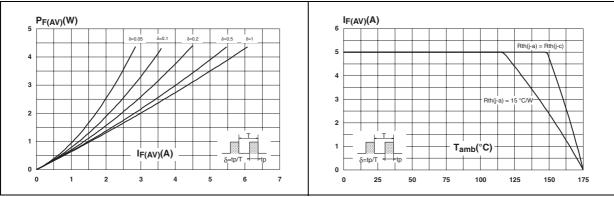


Figure 3. Normalized avalanche power derating versus pulse duration

Figure 4. Normalized avalanche power derating versus junction temperature

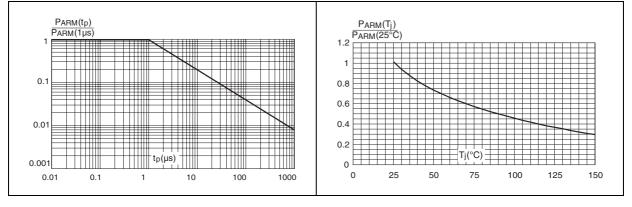


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 6. Relative variation of thermal impedance junction to ambient versus pulse duration

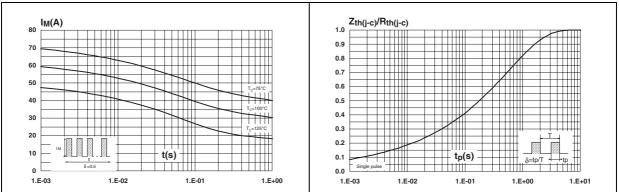
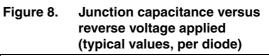


Figure 7. Reverse leakage current versus reverse voltage applied (typical values, per diode)



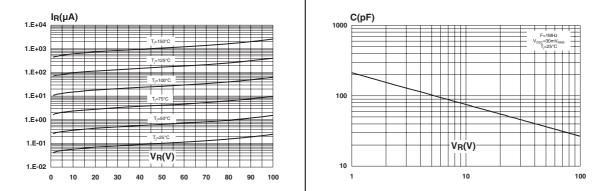
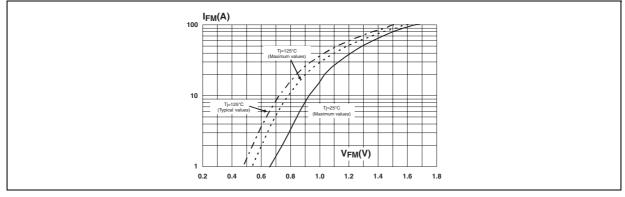


Figure 9. Forward voltage drop versus forward current (per diode)

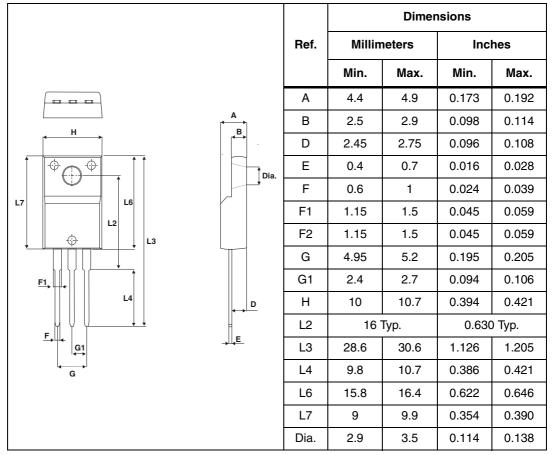


2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 N·m to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in ECOPACK[®] packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at *www.st.com*.

Table 5. TO-220FPAB 3 leads in-line dimensions



3 Ordering information

Table 6.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS10LCD100CFP	STPS10LCD100C	TO-220FPAB	2.0 g	50	Tube

4 Revision history

Table 7.Document revision history

Date	Revision	Description of changes
23-May-2008	1	First issue.



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